NGTB15N60EG

IGBT - Short-Circuit Rated

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Non−Punch Through (NPT) Trench construction, and provides superior performance in demanding switching applications. Offering both low on state voltage and minimal switching loss, the IGBT is well suited for motor drive control and other hard switching applications. Incorporated into the device is a rugged co−packaged reverse recovery diode with a low forward voltage.

Features

- Low Saturation Voltage Resulting in Low Conduction Loss
- Low Switching Loss in Higher Frequency Applications
- Soft Fast Reverse Recovery Diode
- 10 μs Short Circuit Capability
- Excellent Current versus Package Size Performance Density
- This is a Pb−Free Device

Typical Applications

- White Goods Appliance Motor Control
- General Purpose Inverter
- AC and DC Motor Control

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−emitter voltage	V_{CES}	600	V
Collector current @ T_C = 25°C @ T_C = 100°C	I_C	 30 15	A
Pulsed collector current, T_{pulse} limited by T_{Jmax}	I_{CM}	120	A
Diode forward current @ T_C = 25°C @ T_C = 100°C	I_F	 30 15	A
Diode pulsed current, T_{pulse} limited by T_{Jmax}	I_{FM}	120	A
Gate−emitter voltage	V_{GE}	±20	V
Power dissipation @ T_C = 25°C @ T_C = 100°C	P_D	 117 47	W
Short circuit withstand time V_{GE} = 15 V, V_{CE} = 400 V, $T_J \leq$ +150°C	t_{SC}	10	μs
Operating junction temperature range	T_J	−55 to +150	°C
Storage temperature range	T_{stg}	−55 to +150	°C
Lead temperature for soldering, 1/8” from case for 5 seconds	T_{SLD}	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

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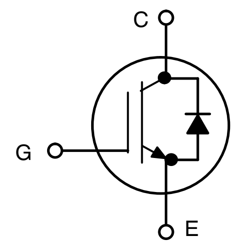
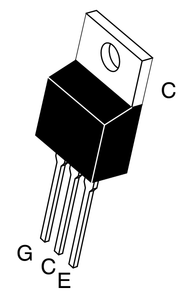
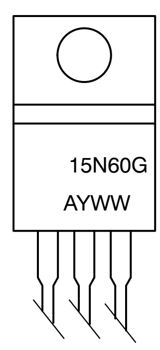
15 A, 600 V
V_{CEsat} = 1.7 V





TO−220
CASE 221A
STYLE 9

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB15N60EG	TO−220 (Pb−Free)	50 Units / Rail

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction to case, for IGBT	$R_{\theta JC}$	1.06	°C/W
Thermal resistance junction to case, for Diode	$R_{\theta JC}$	3.76	°C/W
Thermal resistance junction to ambient	$R_{\theta JA}$	60	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
STATIC CHARACTERISTIC						
Collector−emitter breakdown voltage, gate−emitter short−circuited	V_{GE} = 0 V, I_C = 500 μA	$V_{(BR)CES}$	600	–	–	V
Collector−emitter saturation voltage	V_{GE} = 15 V , I_C = 15 A V_{GE} = 15 V , I_C = 15 A, T_J = 150°C	V_{CEsat}	1.45 1.8	1.7 2.1	1.95 2.4	V
Gate−emitter threshold voltage	V_{GE} = V_{CE} , I_C = 250 μA	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector−emitter cut−off current, gate−emitter short−circuited	V_{GE} = 0 V, V_{CE} = 600 V V_{GE} = 0 V, V_{CE} = 600 V, T_J = 150°C	I_{CES}	– –	10 –	– 200	μA
Gate leakage current, collector−emitter short−circuited	V_{GE} = 20 V, V_{CE} = 0 V	I_{GES}	–	–	100	nA
Forward Transconductance	V_{CE} = 20 V, I_C = 15 A	g_{fs}	–	10.1	–	S
DYNAMIC CHARACTERISTIC						
Input capacitance	V_{CE} = 20 V, V_{GE} = 0 V, f = 1 MHz	C_{ies}	–	2600	–	pF
Output capacitance		C_{oes}	–	64	–	
Reverse transfer capacitance		C_{res}	–	42	–	
Gate charge total	V_{CE} = 480 V, I_C = 15 A, V_{GE} = 15 V	Q_g	–	80	–	nC
Gate to emitter charge		Q_{ge}	–	24	–	
Gate to collector charge		Q_{gc}	–	33	–	
SWITCHING CHARACTERISTIC , INDUCTIVE LOAD						
Turn−on delay time	T_J = 25°C V_{CC} = 400 V, I_C = 15 A R_g = 22 Ω V_{GE} = 0 V / 15 V	$t_{d(on)}$	–	78	–	ns
Rise time		t_r	–	30	–	
Turn−off delay time		$t_{d(off)}$	–	130	–	
Fall time		t_f	–	120	–	
Turn−on switching loss		E_{on}	–	0.900	–	mJ
Turn−off switching loss		E_{off}	–	0.300	–	
Total switching loss		E_{ts}	–	1.200	–	
Turn−on delay time	T_J = 150°C V_{CC} = 400 V, I_C = 15 A R_g = 22 Ω V_{GE} = 0 V / 15 V	$t_{d(on)}$	–	76	–	ns
Rise time		t_r	–	33	–	
Turn−off delay time		$t_{d(off)}$	–	133	–	
Fall time		t_f	–	223	–	
Turn−on switching loss		E_{on}	–	1.10	–	mJ
Turn−off switching loss		E_{off}	–	0.510	–	
Total switching loss		E_{ts}	–	1.610	–	
DIODE CHARACTERISTIC						
Forward voltage	V_{GE} = 0 V, I_F = 15 A V_{GE} = 0 V, I_F = 15 A, T_J = 150°C	V_F	– –	1.6 1.6	1.85 –	V

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
DIODE CHARACTERISTIC						
Reverse recovery time	T_J = 25°C I_F = 15 A, V_R = 200 V di_F/dt = 200 A/μs	t_{rr}	–	270	–	ns
Reverse recovery charge		Q_{rr}	–	350	–	nc
Reverse recovery current		I_{rrm}	–	5	–	A
Reverse recovery time	T_J = 125°C I_F = 15 A, V_R = 200 V di_F/dt = 200 A/μs	t_{rr}	–	350	–	ns
Reverse recovery charge		Q_{rr}	–	1000	–	nc
Reverse recovery current		I_{rrm}	–	7.5	–	A

TYPICAL CHARACTERISTICS

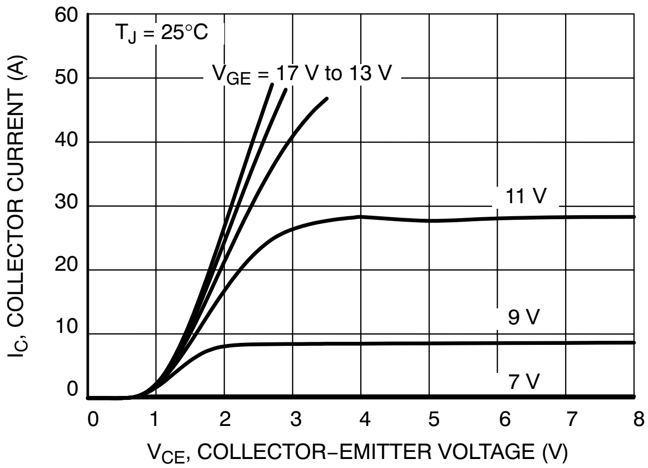


Figure 1. IGBT Output Characteristics

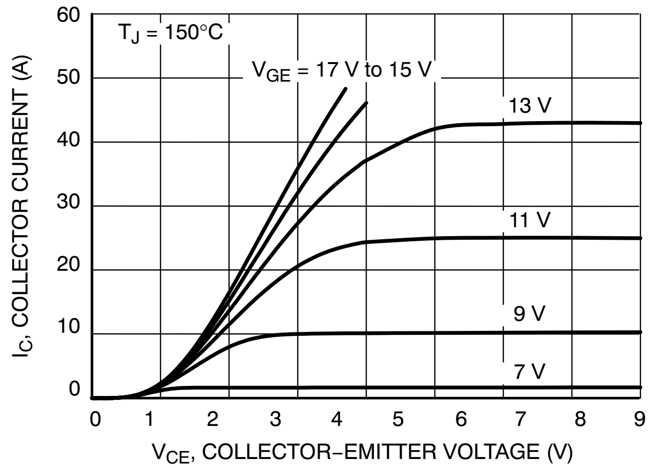


Figure 2. IGBT Output Characteristics

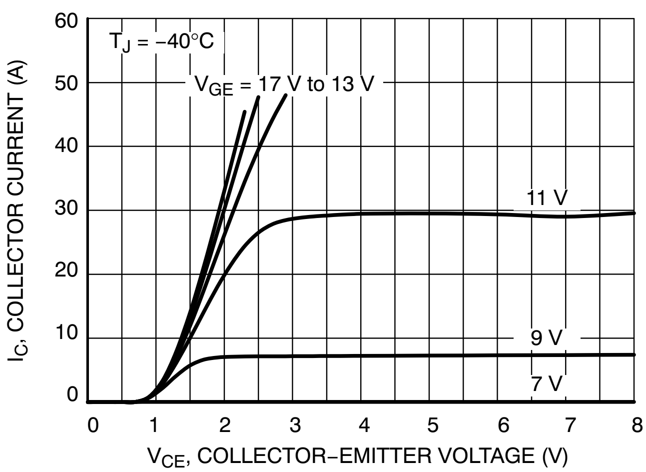


Figure 3. IGBT Output Characteristics

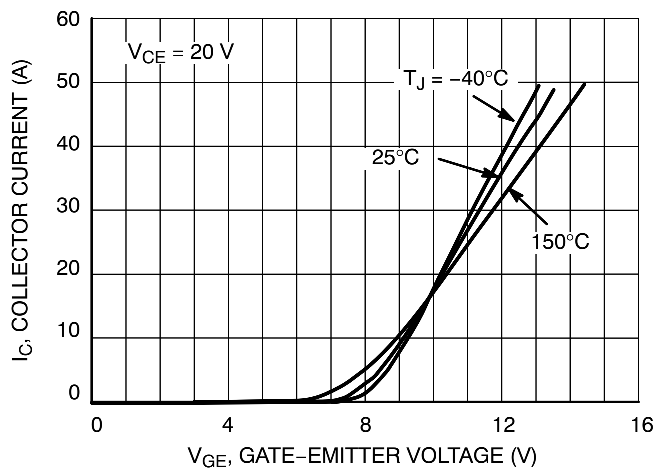


Figure 4. Typical Transfer Characteristics

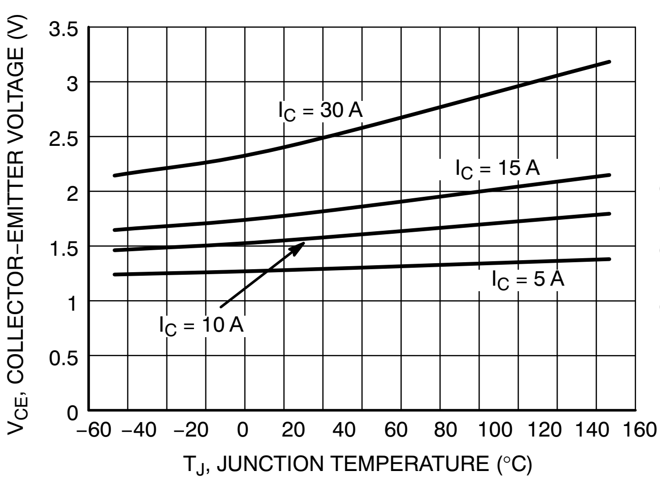


Figure 5. $V_{CE(sat)}$ vs. T_J

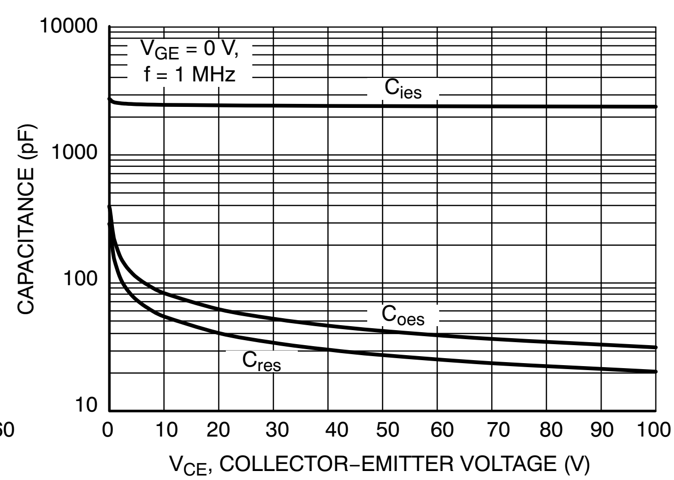


Figure 6. Typical Capacitance

TYPICAL CHARACTERISTICS

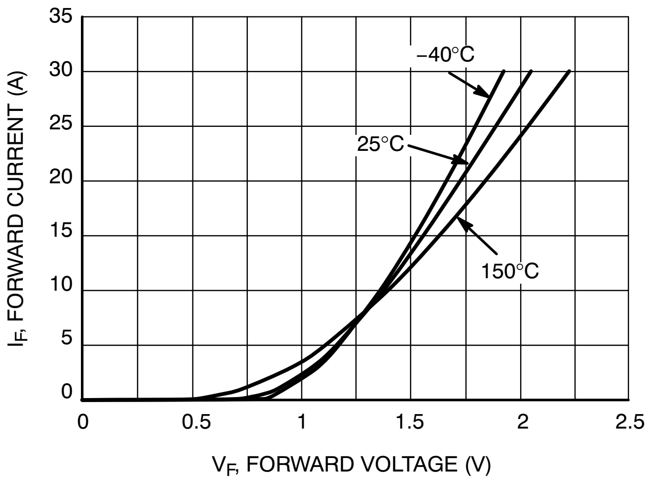


Figure 7. Diode Forward Characteristics

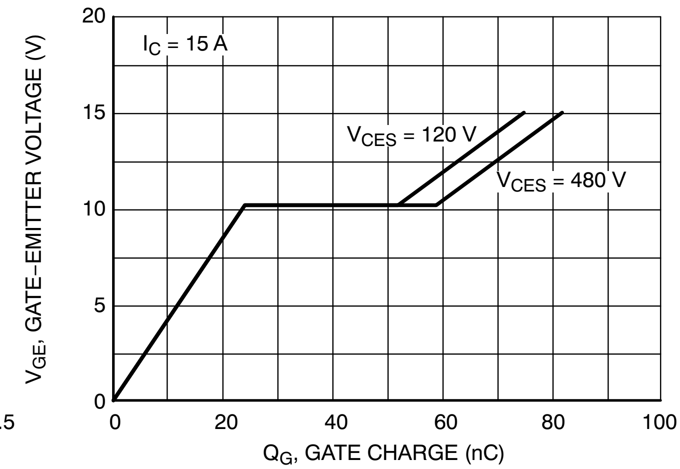


Figure 8. Typical Gate Charge

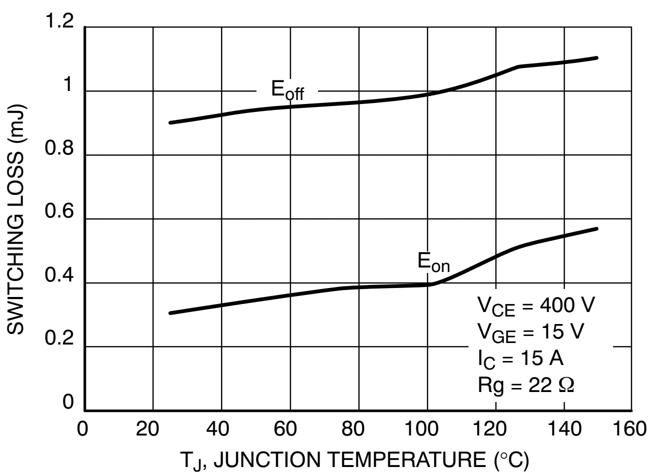


Figure 9. Switching Loss vs. Temperature

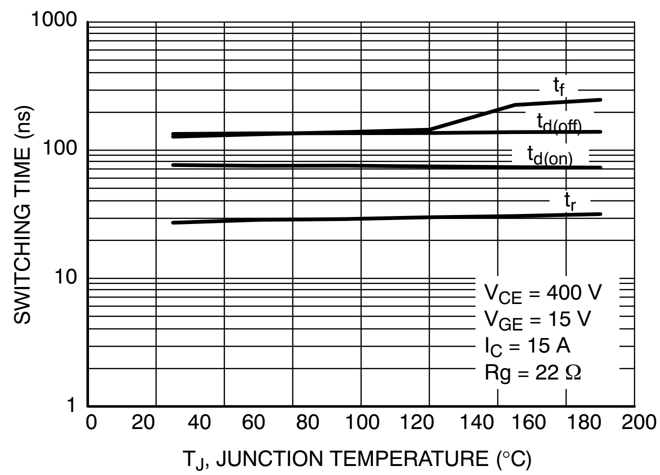


Figure 10. Switching Time vs. Temperature

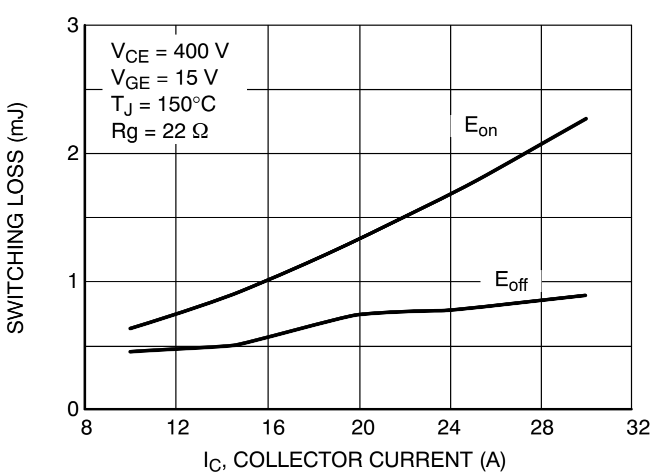


Figure 11. Switching Loss vs. I_C

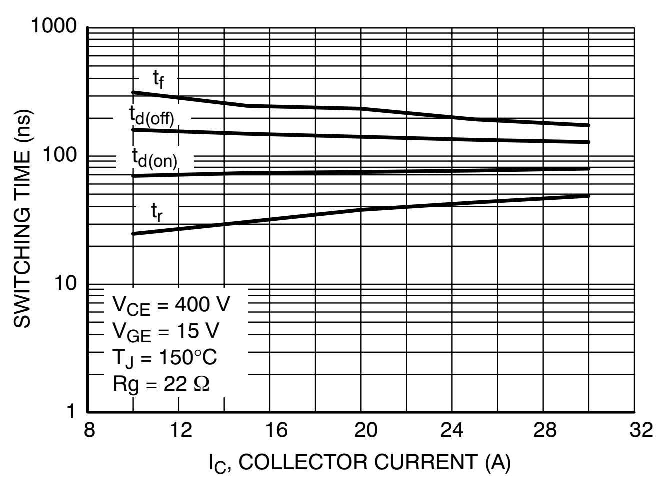


Figure 12. Switching Time vs. I_C

TYPICAL CHARACTERISTICS

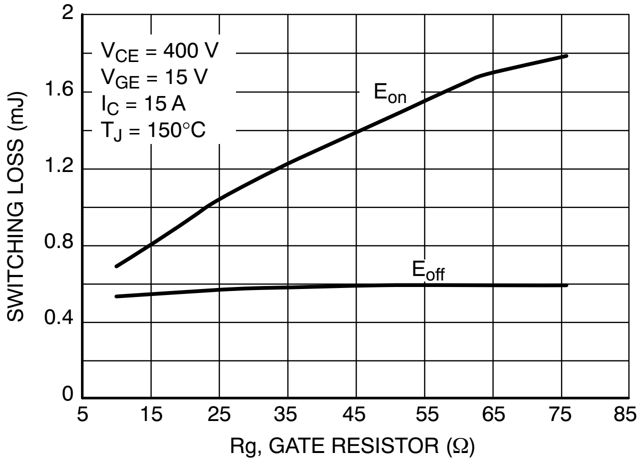


Figure 13. Switching Loss vs. Rg

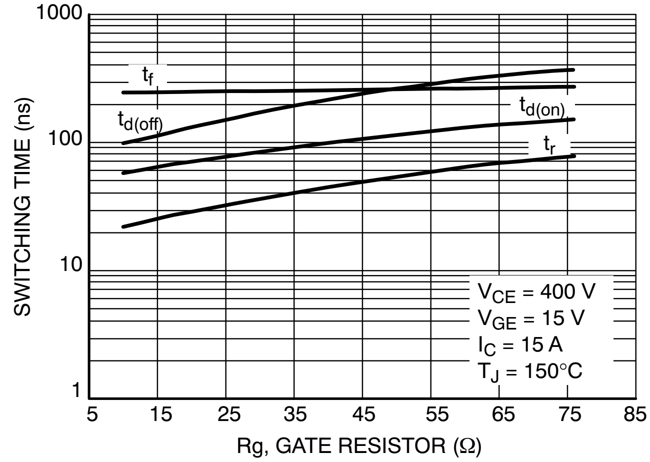


Figure 14. Switching Time vs. Rg

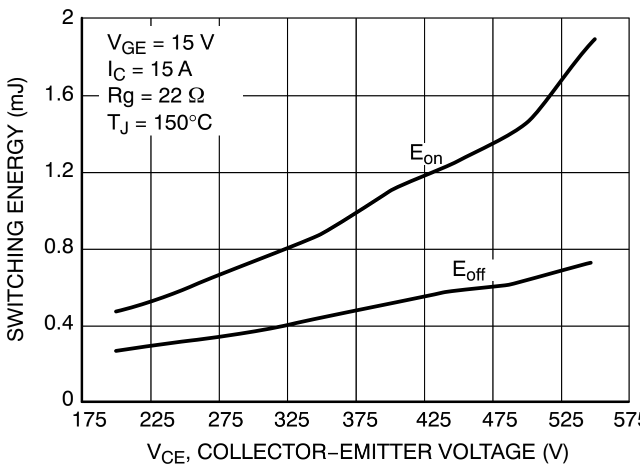


Figure 15. Switching Loss vs. V_{CE}

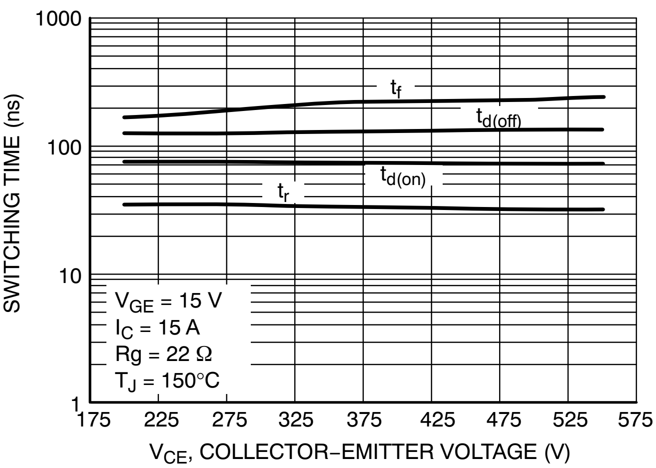


Figure 16. Switching Time vs. Collector−Emitter Voltage

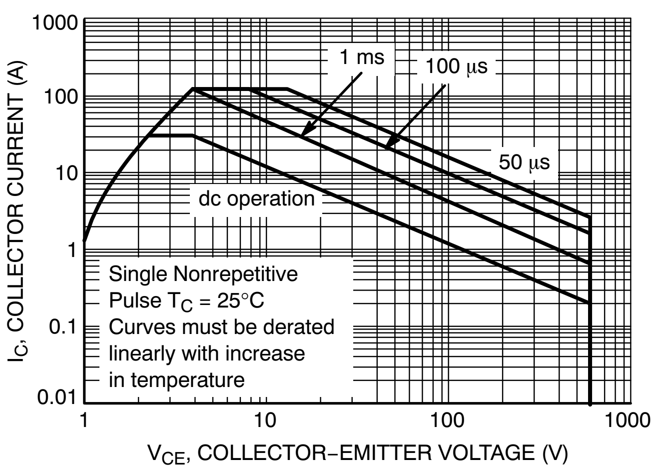


Figure 17. Safe Operating Area

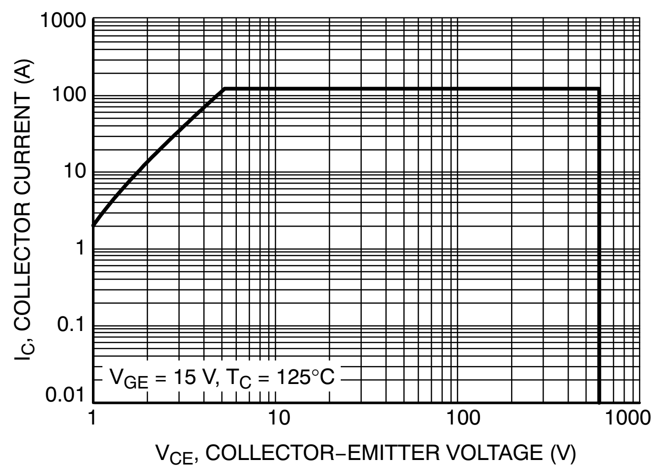
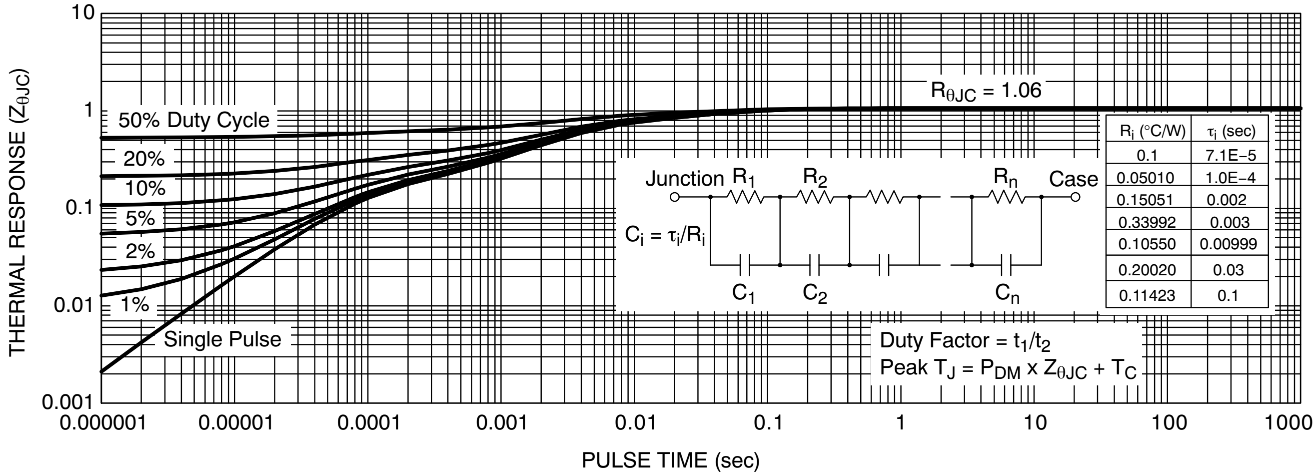


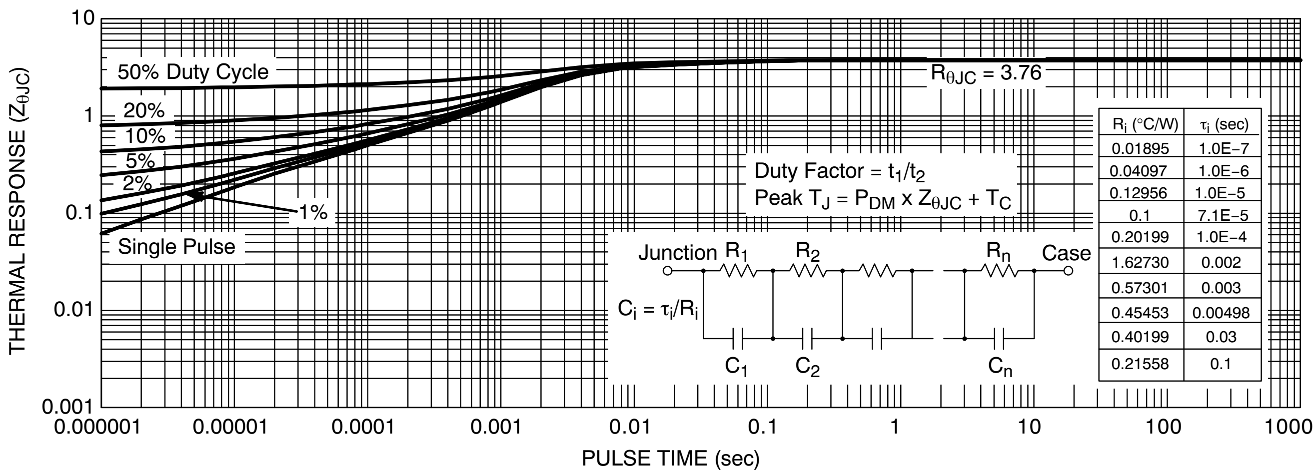
Figure 18. Reverse Bias Safe Operating Area

TYPICAL CHARACTERISTICS



R_i (°C/W)	τ_i (sec)
0.1	7.1E−5
0.05010	1.0E−4
0.15051	0.002
0.33992	0.003
0.10550	0.00999
0.20020	0.03
0.11423	0.1

Figure 19. IGBT Transient Thermal Impedance



R_i (°C/W)	τ_i (sec)
0.01895	1.0E−7
0.04097	1.0E−6
0.12956	1.0E−5
0.1	7.1E−5
0.20199	1.0E−4
1.62730	0.002
0.57301	0.003
0.45453	0.00498
0.40199	0.03
0.21558	0.1

Figure 20. Diode Transient Thermal Impedance

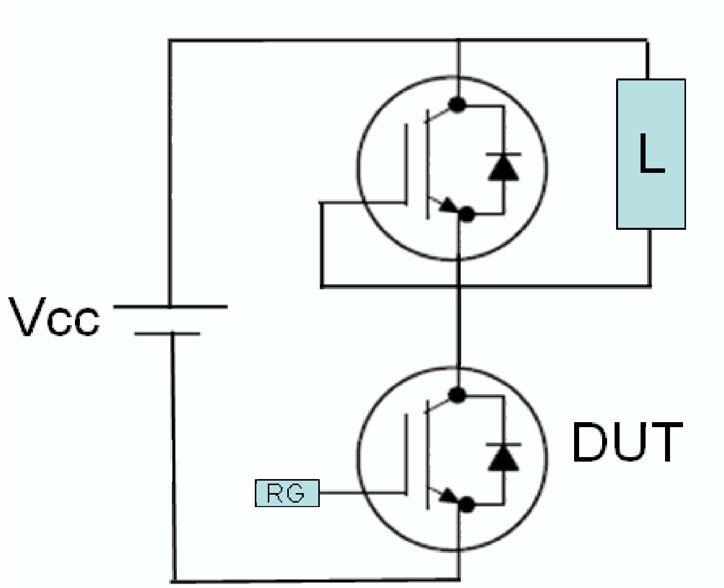


Figure 21. Test Circuit for Switching Characteristics

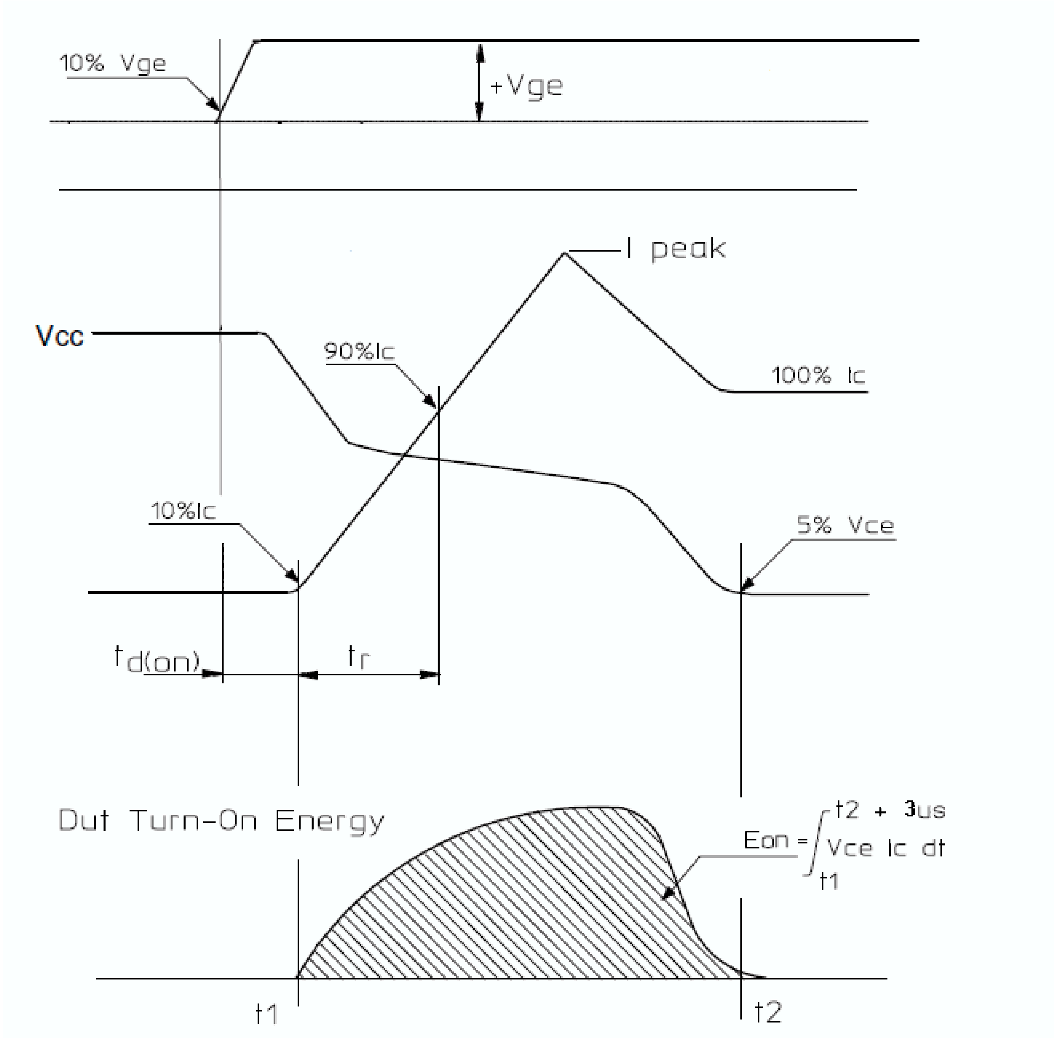


Figure 22. Definition of Turn On Waveform

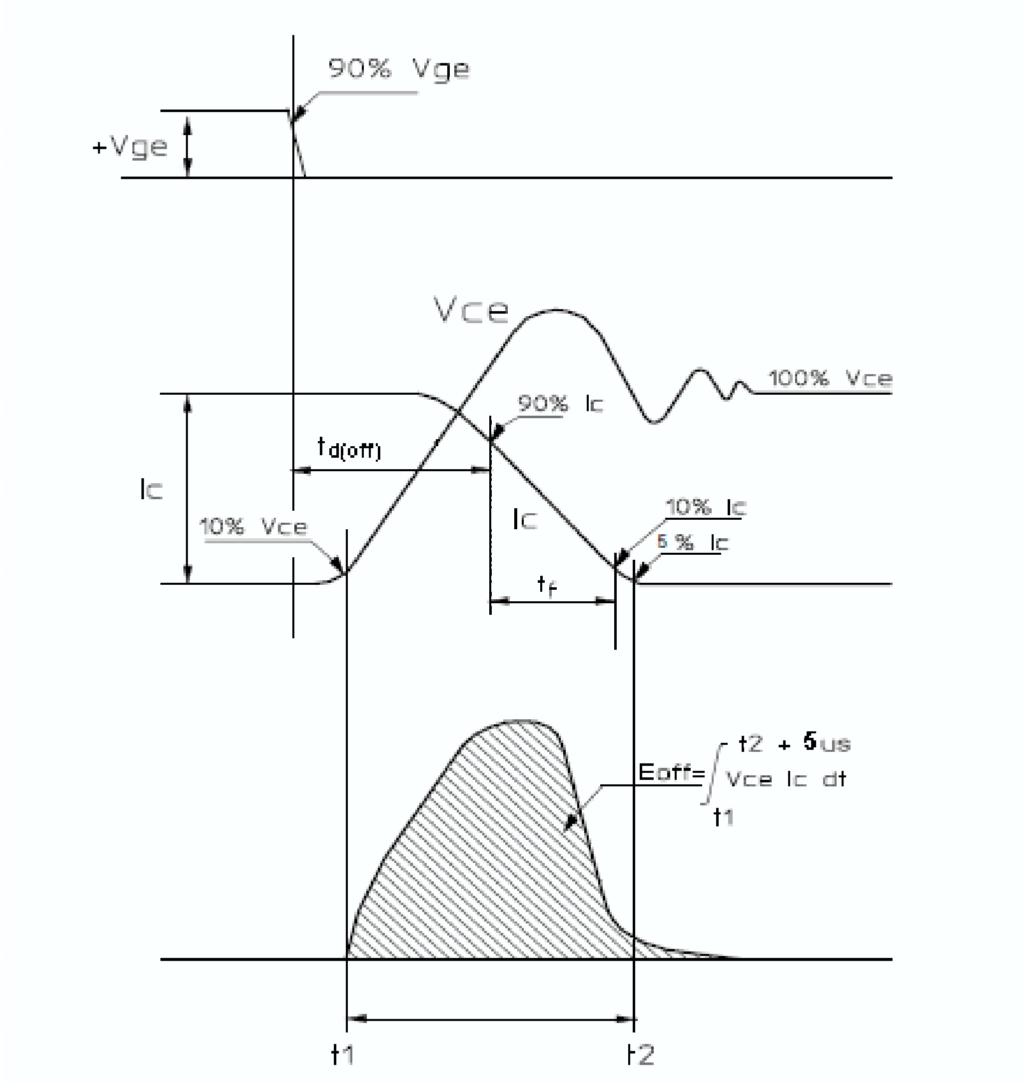
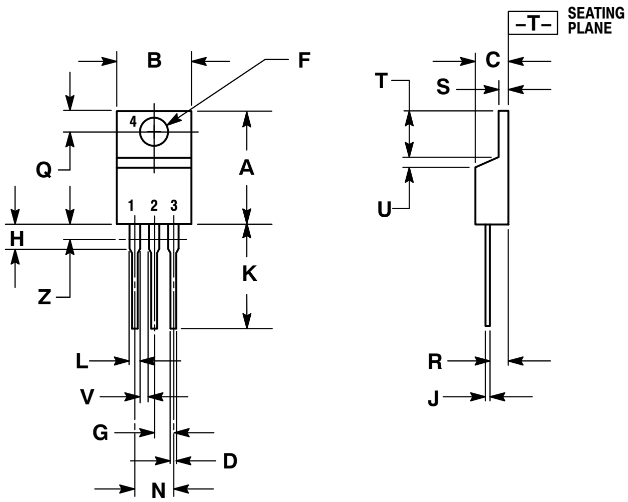


Figure 23. Definition of Turn Off Waveform

PACKAGE DIMENSIONS

TO−220
CASE 221A−09
ISSUE AG



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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